

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. Low VF.
2. High reliability.
3. High Surge proof resistivity.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage power supply rectifier.
2. High voltage rectifier circuit for microwave oven.
3. Other.

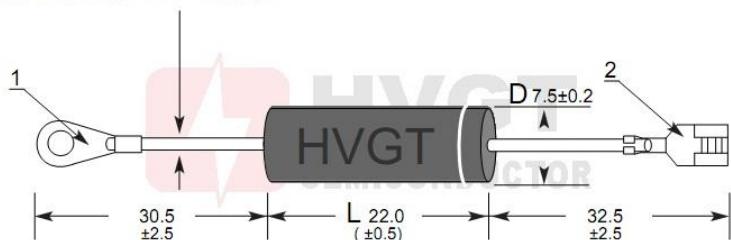
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.90 grams (approx).

SHAPE DISPLAY:

SIZE: (Unit:mm)
HVGT NAME: DO-722B
DO-722B Series

Lead Diameter 1.2mm ±0.02



1. Flat quick-connect terminal CSS-66325-F
2. Crimp-type terminal lugs for copper conductor 1.25-4M

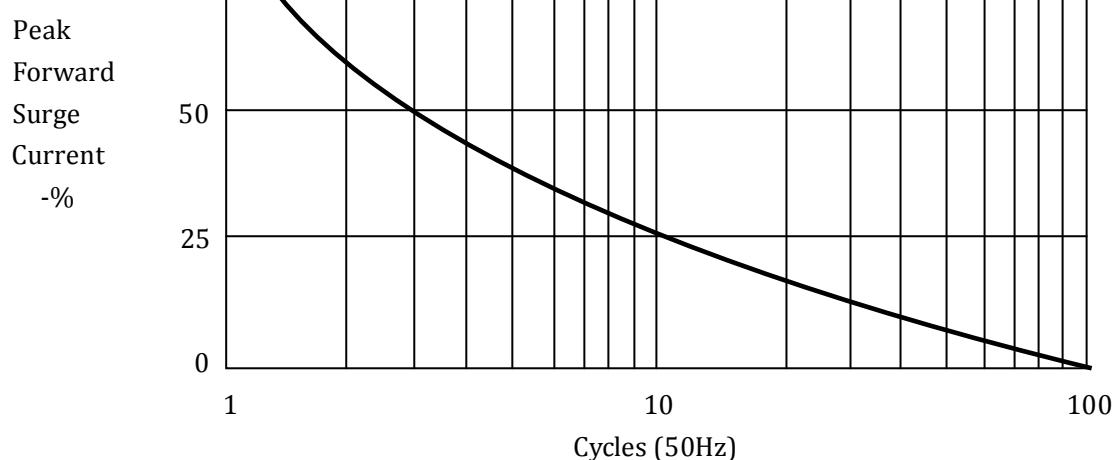
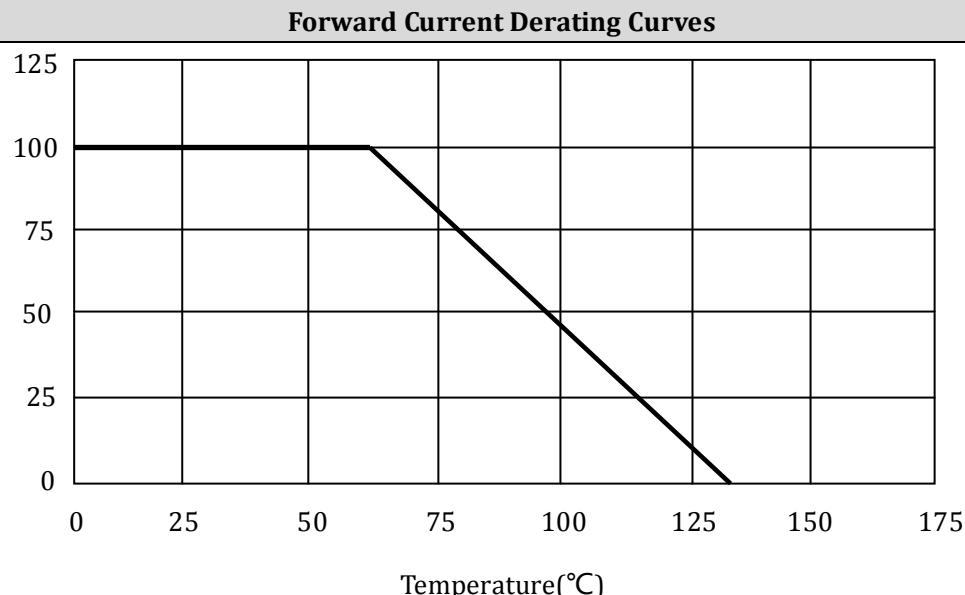
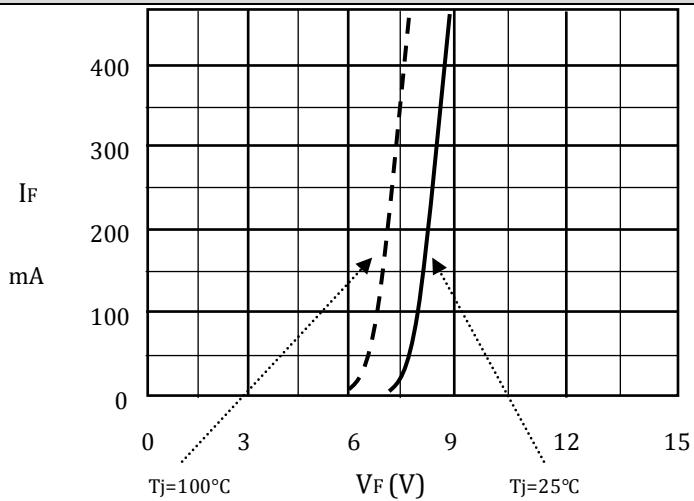
Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V _{RRM}	T _A =25°C	12	kV
Average Forward Current Maximum	I _o	T _A =60°C	350	mA
Non-repetitive Peak Forward Current	I _{FSR}	T _A =25°C; W _p =1mS.Rectangular-wave. One-shot	100	mA
Non-repetitive Peak Reverse Current	I _{FR}	T _A =25°C; 50HzSine half-wave peak value.One-shot.	30	A
Junction Temperature	T _J		130	°C
Allowable Operation Case Temperature	T _c		-40~+130	°C
Storage Temperature	T _{STG}		-55~+150	°C

ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data Value	Units
Maximum Forward Voltage Drop	V _{FM}	at 25°C; at I _o	10	V
Maximum Reverse Current	I _{R1}	at 25°C; at V _{RRM}	5.0	uA
	I _{R2}	at 100°C; at V _{RRM}	50	uA
Maximum Reverse Recovery Time	T _{RR}	at 25°C; I _F =0.5I _R ; I _R =I _{FAVM} ; I _{RR} =0.25I _R	--	nS
Minimum Avalanche Breakdown Voltage	V _Z	I _R =100uA	12.5	kV


Forward Characteristics

Reverse Characteristics
